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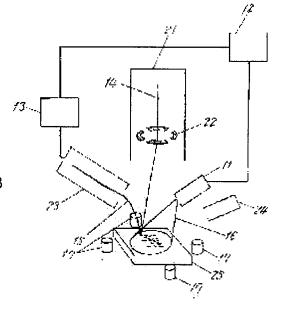
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## (54) SEMICONDUCTOR ANALYSIS DEVICE AND ANALYSIS METHOD

## (57) Abstract:

PROBLEM TO BE SOLVED: To solve the problem of inability to detect the potential difference among P-N junctions due to the charging of an interface level in a conventional Auger electron spectroscope.

SOLUTION: A constitution, where a function 11 for irradiating a sample surface with a light having energy larger than the band gap of a sample and smaller than the work function of the sample and functions 12 and 13 modulating light intensity and detecting the fluctuation components of Auger electron intensity synchronized with light intensity added in addition to the function of a conventional Auger electron spectral device are added, is arranged. Plural photodetectors, which adjust an optical axis, are arranged near the optical axis of light irradiating the sample surface.



## **LEGAL STATUS**

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